



INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: 150.01170103	Serial No.: 10/669,384
	Applicant(s): Basceri et al.	Confirmation No.: Unassigned 3937
	Application Filing Date: September 24, 2003	Group: Unassigned Art Unit 2811
	Information Disclosure Statement mailed: December <u>22</u> , 2003	

U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
A.O.A.		5,270,241	12/14/93	Dennison et al.			
A.O.A.		5,555,486	09/10/96	Kingon et al.			
A.O.A.		6,117,689	09/12/00	Summerfelt			
A.O.A.		6,333,537	12/25/01	Arita			
A.O.A.		6,337,239	01/08/02	Dehm et al.			
A.O.A.		6,372,291	04/16/02	Hua et al.			
A.O.A.		6,482,736	11/19/02	Basceri et al.			
A.O.A.		6,534,357	03/18/03	Basceri et al.			
A.O.A.		US 2003/0001190 A1	01/02/03	Basceri et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		None						

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copy Enclosed	Document Description
A.O.A.	X	McGuire, "Semiconductor Materials and Process Technology Handbook," Noyes Publ., Nowich, NY, 1988: 291.
A.O.A.	X	Oh et al., "Thermal Stability of RuO ₂ /Ru Bilayer Thin Film in Oxygen Atmosphere," <i>Thin Solid Films</i> , 2000;359: 118-123.
A.O.A.		Yoon et al., "Investigation of RuO ₂ - Incorporated PT layer as a Bottom Electrode and Diffusion Barrier for High Epsilon Capacitor Applications," <i>Electrochem. and Solid-State Lett</i> , 2000;3(8):373-376.

EXAMINER <i>a.o.a.</i>	Date Considered <i>21 June 2006</i>
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	